

a marked up version has not been changed relative to the immediate prior version, except that marked up versions are not being supplied for any canceled claim.

60. (Cancelled).

61. (Cancelled).

62. (Cancelled).

63. (Cancelled).

68. (Amended) A capacitor construction, comprising:

a storage node extending within an insulative layer, at least a portion of the storage node extending along and against a material that comprises from about 2% to about 20% carbon (by weight);

a second electrode proximate the storage node; and

a dielectric layer between the second electrode and the storage node.

69. (Cancelled).

B2
70. (Amended) The capacitor construction of claim 68 wherein the material comprises silicon and carbon.

B3
76. (Amended) A DRAM construction, comprising:
a pair of wordlines over a substrate, the wordlines comprising sidewall edges;
sidewall spacers extending along the sidewall edges of the wordlines;
three nodes proximate the wordlines, the three nodes comprising a first node, second node and third node, the second node being in gated electrical connection with the first node through one of the wordlines and being in gated electrical connection with the third node through the other of the wordlines;
a carbon-containing material proximate the wordlines, the carbon-containing material comprising from about 2% to about 20% carbon;
an insulative layer over the etch stop;
a first capacitor construction in electrical connection with the first node, the first capacitor construction comprising a first storage node;
a second capacitor construction in electrical connection with the third node, the second capacitor construction comprising a second storage node; and
a bit line contact in electrical connection with the second node, at least one of the first storage node, second storage node and bit line contact being in physical contact with the carbon-containing material.

B7
79. (Amended) The DRAM construction of claim 76 wherein at least the sidewall spacers comprise the carbon-containing material.

82. (Cancelled).

B5
85. (Amended) The DRAM construction of claim 76 wherein the carbon-containing material comprises silicon, nitrogen and carbon.

86. (Amended) The DRAM construction of claim 76 wherein the carbon-containing material consists essentially of silicon, nitrogen and carbon.